

ABSOLUTE MAXIMUM RATINGS

SUPPLY VOLTAGE, $+V_S$ to $-V_S$	350V
OUTPUT CURRENT, continuous	60mA
INPUT VOLTAGE, differential	$\pm 16V$
INPUT VOLTAGE, common mode	$\pm V_S$
TEMPERATURE, junction	150°C

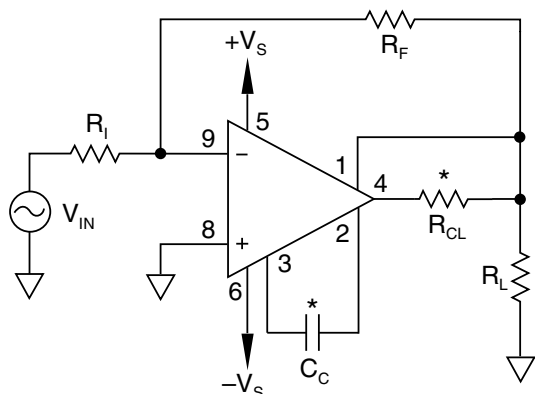
NOTE: Refer to parent product data sheet PA241 for typical AC electrical characteristics, precautions, applications and other test parameters.

DC WAFER PROBED SPECIFICATIONS

PARAMETER	TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
OFFSET VOLTAGE, initial	$V_S = \pm 50V$		15	40	mV
BIAS CURRENT, initial			56	200	pA
COMMON MODE REJECTION	$V_{CM} = \pm 90V$ DC	84	94		dB
VOLTAGE SWING	$I_O = 40mA$	$\pm V_S - 12$	$\pm V_S - 10$		V
SUPPLY CURRENT, quiescent	$V_S = \pm 50V$	1.8	2.1	2.3	mA

NOTES: 1. Unless otherwise stated $V_S = \pm 50V$, $T_A = 25^\circ C$, DC input specification $\pm$ value given.
2. Sample tested by wafer to 95%.

TYPICAL EXTERNAL CONNECTIONS



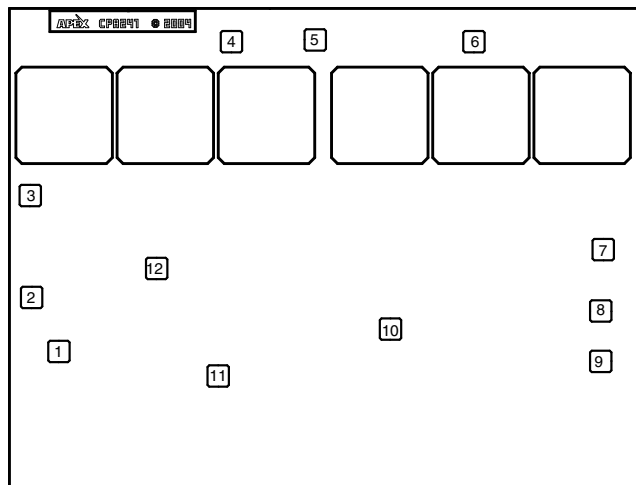
* Required component and value if given.
Optional balance components are recommended values.
 C_C is NPO, rated for full supply voltage $-V_S$ to $+V_S$.

NOTE: Diagram for connection illustration only.
All op amp configurations are possible.

Pad	Function	Pad	Function
1	Output	5	$+V_S$
2	Compensation	6	$-V_S$
3	Compensation	8	$+IN$
4	Current Limit	9	$-IN$

CAUTION The CPA241 is a MOSFET amplifier. ESD handling procedures must be observed

DIE LAYOUT



Dimension: 154.5 x 117.5 $\pm$ 2.5 Mils.

Thickness: 15 Mil (380 μ).

Backside Metal: None, Silicon.

Bond pad: 5 Mil sq (127 μ) Al.

Make no connection to bond pads not listed by function.

Note: The backside of the CPA241 die is isolated up to 500V. The top side walls of the CPA241 die are isolated up to 300V.

Ordering Information:

Order #: CPA241D180:

Die are only available in wafer packages with a total of 80 die per package.